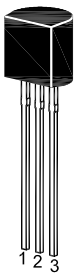
ST 2SA1048

PNP Silicon Epitaxial Planar Transistor

for audio frequency amplifier applications.

The transistor is subdivided into three groups, O, Y and G, according to its DC current gain. As complementary type the NPN transistor ST 2SC2458 is recommended.
On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	150	mA
Base Current	$-I_B$	50	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter			Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 6 V, $-I_C$ = 2 mA	Current Gain Group	O Y G	h_{FE} h_{FE} h_{FE}	70 120 200	140 240 400	- - -
Collector Base Cutoff Current at $-V_{CB}$ = 50 V			$-I_{CBO}$	-	100	nA
Emitter Base Cutoff Current at $-V_{EB}$ = 5 V			$-I_{EBO}$	-	100	nA
Collector Emitter Saturation Voltage at $-I_C$ = 100 mA, $-I_B$ = 10 mA			$-V_{CE(sat)}$	-	0.3	V
Transition Frequency at $-V_{CE}$ = 10 V, $-I_C$ = 1 mA			f_T	80	-	MHz
Output Capacitance at $-V_{CB}$ = 10 V, f = 1 MHz			C_{ob}	-	7	pF